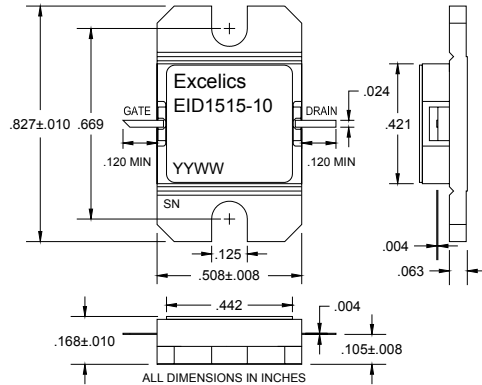


FEATURES

- 15.35– 15.75GHz Bandwidth
- Input/Output Impedance Matched to 50 Ohms
- +40.0 dBm Output Power at 1dB Compression
- 5.5 dB Power Gain at 1dB Compression
- 20% Power Added Efficiency
- Hermetic Metal Flange Package



ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)



Caution! ESD sensitive device.

SYMBOL	PARAMETERS/TEST CONDITIONS ¹	MIN	TYP	MAX	UNITS
P_{1dB}	Output Power at 1dB Compression $f = 15.35\text{-}15.75\text{GHz}$ $V_{DS} = 10\text{ V}, I_{DSQ} \approx 3200\text{mA}$	39.0	40.0		dBm
G_{1dB}	Gain at 1dB Compression $f = 15.35\text{-}15.75\text{GHz}$ $V_{DS} = 10\text{ V}, I_{DSQ} \approx 3200\text{mA}$	4.5	5.5		dB
ΔG	Gain Flatness $f = 15.35\text{-}15.75\text{GHz}$ $V_{DS} = 10\text{ V}, I_{DSQ} \approx 3200\text{mA}$			± 0.6	dB
PAE	Power Added Efficiency at 1dB Compression $f = 15.35\text{-}15.75\text{GHz}$ $V_{DS} = 10\text{ V}, I_{DSQ} \approx 3200\text{mA}$		22		%
I_{d1dB}	Drain Current at 1dB Compression $f = 15.35\text{-}15.75\text{GHz}$		3500	4500	mA
I_{DSS}	Saturated Drain Current $V_{DS} = 3\text{ V}, V_{GS} = 0\text{ V}$		5000	7500	mA
V_P	Pinch-off Voltage $V_{DS} = 3\text{ V}, I_{DS} = 60\text{ mA}$		-1.0	-2.5	V
R_{TH}	Thermal Resistance ²		2.5	3.0	$^\circ\text{C/W}$

Note:

1. Tested with 50 Ohm gate resistor.
2. Overall R_{th} depends on case mounting.

MAXIMUM RATING^{1,2} ($T_a = 25^\circ\text{C}$)

SYMBOLS	PARAMETERS	ABSOLUTE ¹	CONTINUOUS ²
V_{DS}	Drain-Source Voltage	15V	10V
V_{GS}	Gate-Source Voltage	-5V	-3V
I_{gsf}	Forward Gate Current	120mA	40mA
I_{gsr}	Reverse Gate Current	-18mA	-6mA
P_{in}	Input Power	39.0dBm	@ 3dB Compression
T_{ch}	Channel Temperature	175 $^\circ\text{C}$	175 $^\circ\text{C}$
T_{stg}	Storage Temperature	-65 to +175 $^\circ\text{C}$	-65 to +175 $^\circ\text{C}$
P_t	Total Power Dissipation	50W	50W

Note:

1. Exceeding any of the above ratings may result in permanent damage.
2. Exceeding any of the above ratings may reduce MTTF below design goals.

Specifications are subject to change without notice.



EID1515-10

UPDATED 12/21/2006

15.35-15.75 GHz 10-Watt Internally Matched Power FET

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness

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Excelics Semiconductor, Inc. 310 De Guigne Drive, Sunnyvale, CA 94085
Phone: 408-737-1711 Fax: 408-737-1868 Web: www.excelics.com

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